AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A semiconductor laser apparatus comprising a semiconductor laser chip whose bottom is die-bonded to a bonding surface with a conductive die-bonding paste comprising resin, said semiconductor laser chip having a light-emitting point at each of opposed end surfaces thereof,

wherein the conductive die-bonding paste adheres to a lower part of each end surface of the chip, and a highest position of the conductive die-bonding paste on said lower part of each end surface of the semiconductor laser chip is at a height of more than 0.01 mm from the bonding surface and ~~hence~~ from the bottom of the semiconductor laser chip, but is below the light-emitting point of the semiconductor laser chip of the semiconductor laser apparatus.

2. (Original) A semiconductor laser apparatus according to claim 1, wherein said conductive die-bonding paste contains an epoxy resin as a base material.

3. (Original) A semiconductor laser apparatus according to claim 1, wherein said conductive die-bonding paste contains silver flakes as a conductive filler.

4-10. (Canceled)

11. (Previously presented) The apparatus of claim 1, wherein the highest position of the conductive die-bonding paste on said lower part of each end surface is within 0.04 mm of the light-emitting point.

12. (Previously presented) The apparatus of claim 1, wherein the conductive die-bonding paste comprises epoxy resin and at least 80% by weight conductive filler of metal particles of flakes.

13. (Previously presented) A semiconductor laser apparatus comprising:

a semiconductor laser chip die-bonded to a bonding surface with a conductive die-bonding paste, said semiconductor laser chip having a light-emitting point at at least one end surface thereof so as to provide a semiconductor laser apparatus,

wherein a highest position at which the conductive die-bonding paste adheres to at least one end surface of the semiconductor laser chip is at a height of more than 0.01 mm from the bonding surface, but is below the light-emitting point of the semiconductor laser chip; and

wherein the conductive die-bonding paste comprises epoxy resin and at least 80% by weight conductive filler of metal particles or flakes.

14. (Previously presented) A semiconductor laser apparatus for use in an optical pickup using a three-beam scheme for optical disks, the semiconductor laser apparatus comprising:

a semiconductor laser chip whose bottom is die-bonded to a bonding surface with a conductive die-bonding paste, said semiconductor laser chip of the semiconductor laser apparatus including a light-emitting point at each of opposed end surfaces thereof,

wherein the conductive die-bonding paste adheres to a lower part of each end surface of the chip from the bottom up to a height below the light emitting point so that when the apparatus is used in the optical pickup an auxiliary beam directed from an optical disk to the lower part of one of the end surfaces is scattered by the conductive die-bonding paste adhering thereto.

15. (Previously presented) The apparatus of claim 14, wherein a highest position of the conductive die-bonding paste on said lower part of each end surface of the chip is at a height of more than 0.01 mm from the bottom of the chip.

16. (Previously presented) The apparatus of claim 14, wherein a highest position of the conductive die-bonding paste on said lower part of each end surface of the chip is within 0.04 mm of the light emitting point.